

# Erasable superconductivity in topological insulator $\text{Bi}_2\text{Se}_3$ induced by voltage pulse

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## Article

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2 induced by voltage pulse

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14 **Three-dimensional topological insulators (TIs) attract much attention due to**  
15 **its topologically protected Dirac surface states [1, 2, 3, 4]. Doping into TIs or**  
16 **their proximity with normal superconductors can promote the realization of topo-**  
17 **logical superconductivity (SC) and Majorana fermions with potential applications**  
18 **in quantum computations [5, 6, 7, 8, 9, 10, 11]. Here, we observed an emergent**  
19 **superconductivity in local mesoscopic point-contacts on the topological insulator**  
20  **$\text{Bi}_2\text{Se}_3$  by applying a voltage pulse through the contacts, evidenced by the Andreev**  
21 **reflection peak in the point-contact spectra and a visible resistance drop in the four-**  
22 **probe electrical resistance measurements. More intriguingly, the superconductivity**  
23 **can be erased with thermal cycles by warming up to high temperatures (300 K)**  
24 **and induced again by the voltage pulse at the base temperature (1.9 K), suggest-**  
25 **ing a significance for designing new types of quantum devices. Nematic behaviour**

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26 **is also observed in the superconducting state, similar to the case of  $\text{Cu}_x\text{Bi}_2\text{Se}_3$  as**  
27 **topological superconductor candidates [12, 13, 14, 15, 16, 11, 17, 18].**

28 So far, various methods such as doping, proximity effect, hydraulic pressure, tip-contact have  
29 been applied on nontrivial topological materials in order to induce topological superconductivity  
30 and Majorana fermions [10, 6, 7, 8, 19, 20, 21]. Majorana fermions are proposed to play a crucial  
31 role in the fault-tolerant quantum computation [22, 23, 24]. Among them,  $\text{Bi}_2\text{Se}_3$  has served  
32 as a characteristic compound of topological insulators susceptible to tuning and emergence of  
33 superconductivity [10, 6, 19] and its van der Waals (vdW) structure also implies a potential  
34 application in quantum electronic devices, especially when superconductivity can be achieved  
35 [25, 26, 27]. However, an easy and controllable condition to realize SC in  $\text{Bi}_2\text{Se}_3$  is still lacking  
36 and thus desirable.

37 In this paper, an unambiguous superconductivity is observed for the mesoscopic point-  
38 contacts on topological insulator  $\text{Bi}_2\text{Se}_3$  after applying a voltage pulse, evidenced by the Andreev  
39 reflection peak in point-contact spectra (PCS) and a resistance drop for the exfoliated  $\text{Bi}_2\text{Se}_3$   
40 flake samples. Superconductivity emerges only in the case of Ag- $\text{Bi}_2\text{Se}_3$  contacts with either  
41 silver paints in soft-PCS(SPCS) or Ag tips in mechanical-PCS(MPCS) right after the voltage  
42 pulse, but is absent for the Au, Cu or Ti tips, favoring the scenario that the emergent SC is  
43 probably due to Ag dopants into the vdW gap of  $\text{Bi}_2\text{Se}_3$  across the interface. The SC becomes  
44 unstable against thermal cycles and disappears when the sample is warmed up to high temper-  
45 atures, however, it can be re-induced by a new voltage pulse after cooled back to 1.9 K. Our  
46 observations strongly support the erasable nature of the SC in the local contact region, ensuring  
47 potential applications in quantum devices.

48 The  $\text{Bi}_2\text{Se}_3$  crystal is composed of alternating Se-Bi-Se-Bi-Se quintuple layers as shown in  
49 Fig. 1a and there exists a weak vdW gap between adjacent quintuple layers, making this material  
50 easy to be exfoliated as other vdW materials. Temperature dependent resistivity of  $\text{Bi}_2\text{Se}_3$  with  
51 a sample size of  $1073 \mu\text{m} \times 591 \mu\text{m} \times 6.3 \mu\text{m}$  is shown in Fig. 1b, which has a slight upturn due  
52 to its insulating band gap but saturates below 40 K with its gapless surface state, consistent with  
53 previous reports [28, 29]. Soft point-contacts are formed by silver paints on  $\text{Bi}_2\text{Se}_3$  as in Fig. 1c,  
54 same as the soft-PCS configuration on  $\text{Cu}_x\text{Bi}_2\text{Se}_3$  [30]. Fig. 1d shows the soft-PCS conductance  
55 curve on  $\text{Bi}_2\text{Se}_3$  at 1.9 K and only an asymmetric background is observed in the absence of any  
56 special features. Interestingly, when a voltage pulse between 4 -10 V with a pulse duration less  
57 than 10 ms is applied across the contacts, a reproducible zero-bias conductance peak (ZBCP)  
58 can be observed with dips at high bias voltages as in Fig. 1e. Fig. 1f shows the evolution of  
59 conductance curves in magnetic field and the ZBCP is gradually suppressed without any peak  
60 splitting and finally disappears around 3.0 T. Moreover, the ZBCP gets weaker in intensity with  
61 increased temperatures until around 4.5 K, unambiguously signaling the Andreev reflections

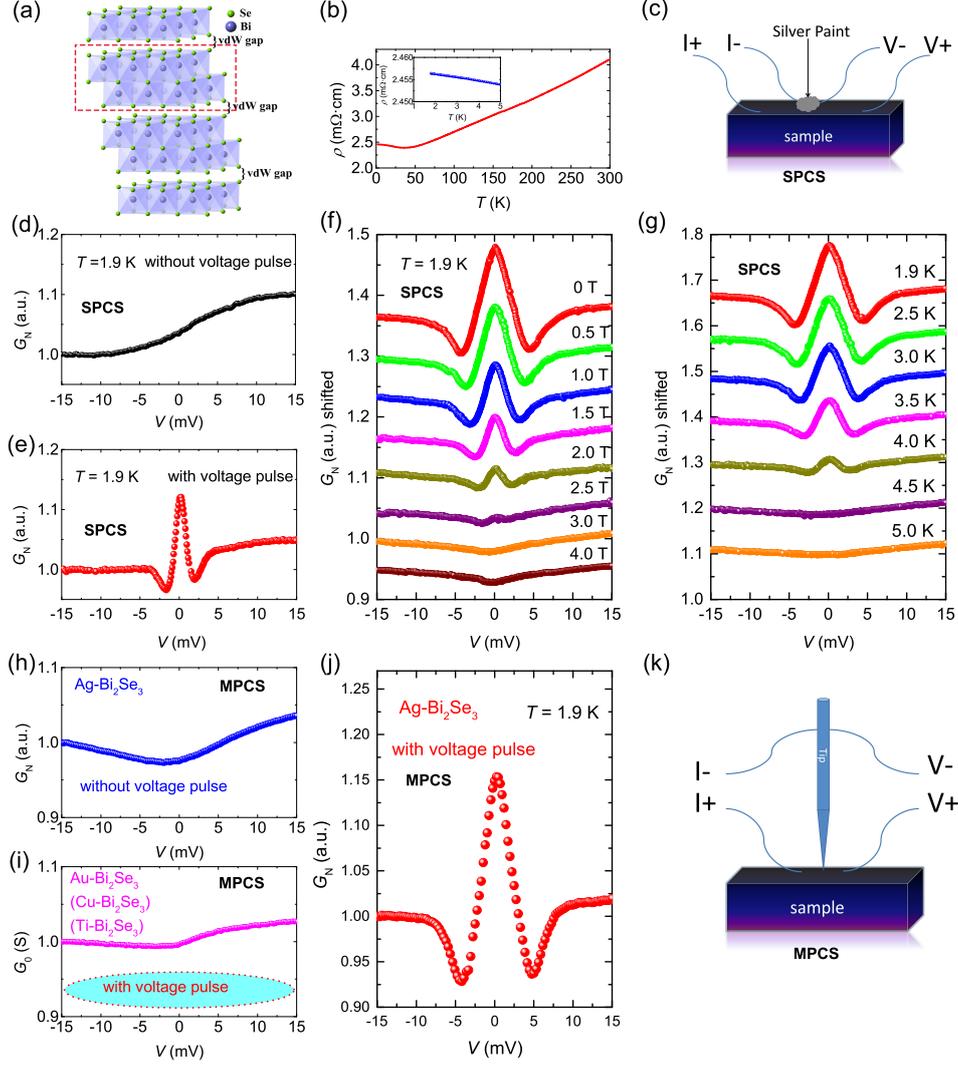


Figure 1: **Evidence for induced superconductivity in mesoscopic Ag point-contact on  $\text{Bi}_2\text{Se}_3$ .** (a) The crystal structure of topological insulator  $\text{Bi}_2\text{Se}_3$  with vdW gap between adjacent Se-Bi-Se-Bi-Se quintuple layers. (b) Temperature dependence of the electrical resistivity for the pristine  $\text{Bi}_2\text{Se}_3$  sample with a dimension of  $1073 \mu\text{m} \times 591 \mu\text{m} \times 6.3 \mu\text{m}$ . (c) Schematic illustration of the soft-PCS electrode configuration on  $\text{Bi}_2\text{Se}_3$ . (d) A representative soft-PCS conductance curve for silver paint on the  $\text{Bi}_2\text{Se}_3$  crystal at 1.9 K without any voltage pulse.  $G_N$  is the normalized conductance divided by the conductance value at high voltages. (e) A reproducible ZBCP feature in the soft-PCS at 1.9 K after voltage pulse on the contact. (f) & (g) Magnetic field and temperature evolution of the soft-PCS conductance curves with induced superconductivity in the contact region, respectively. (h) & (i) Mechanical-PCS conductance curve at 1.9 K for Ag tip before voltage pulse and for Au, Cu or Ti tip after voltage pulse, respectively. (j) Mechanical-PCS conductance curve at 1.9 K for Ag tip with induced SC after voltage pulse. (k) Schematic illustration of the needle-anvil configuration of mechanical point-contacts.

62 and induced superconductivity in the contact area by voltage pulses [31, 20, 21]. The maximum  
 63 superconducting transition temperature  $T_c$  for all contacts can be as high as 4.5 K as illustrated  
 64 by the temperature dependent conductance curves on  $\text{Bi}_2\text{Se}_3$  in Fig. 1g (or the temperature  
 65 dependent zero-bias conductance (ZBC) in Fig. S1). We note here that the ZBCP only appears  
 66 on the contact affected by the voltage pulse and other contacts without it on the same sample  
 67 would not show any SC trace (Several soft point-contacts on the same sample can be realized  
 68 in practice).

69 In comparison with our soft-PCS results, a needle-anvil type of mechanical-PCS was also  
 70 applied as schematically illustrated in Fig. 1k with several tip options available such as silver,  
 71 gold, copper or titanium. Similar behaviours are observed for the Ag tip on  $\text{Bi}_2\text{Se}_3$  crystals  
 72 after a voltage pulse, where a local SC in the contact can be induced with a characteristic SC  
 73 ZBCP at 1.9 K. In sharp contrast, Au, Cu or Ti tips on  $\text{Bi}_2\text{Se}_3$  fail to induce any SC within the  
 74 maximum voltage pulse  $\sim 10$  V as in Fig. 1i. We would thus speculate that the induced SC in  
 75 the point-contact area is intimately associated with Ag atoms as a result of voltage pulses.

76 In order to confirm the probable superconductivity with electrical resistive measurements,  
 77 the  $\text{Bi}_2\text{Se}_3$  sample was exfoliated by tape to a very tiny flake and it was transferred onto the  
 78 pre-deposited Ag electrodes on the silicon substrate as shown in the inset of Fig. 2a, where  
 79 the space between the neighboring electrode ends is about  $3 \mu\text{m}$  in distance. The temperature  
 80 dependent electrical resistance for the pristine device is shown in Fig. 2a, which also has an  
 81 upturn at low temperatures as in Fig. 1b for the bulk sample. Once voltage pulse is applied on  
 82 the Ag electrodes, a small drop of resistance shows up below 4.5 K ( $\sim 1 - 2\%$ ) as in Fig. 2a,  
 83 implying an induced SC as in the PCS measurements. However, the resistance does not go to  
 84 zero and it is natural to assume a local SC is induced only in the contact region for the  $\text{Bi}_2\text{Se}_3$   
 85 sample. In Fig. 2b, the  $T_c$  decreases with increased magnetic field, and the SC transition is  
 86 totally gone above 2.5 T.

87 It is interesting to study the stability of this local superconductivity against thermal cycles  
 88 and the sample resistance over several thermal cycles with a cooling (warming) speed of 3 K/min  
 89 is shown in Fig. 2c. For the first cycle, the sample is only warmed up to 50 K and then cooled  
 90 back to 1.9 K, where the SC transition temperature  $T_c$  nearly maintains the same value of 4.5  
 91 K with the resistance curves overlapping on each other. However, as long as the sample is  
 92 warmed up to a higher terminal temperature,  $T_c$  is gradually reduced and the transition finally  
 93 disappears after warming up to 300 K. Moreover, superconductivity would emerge once again  
 94 at 1.9 K after a new voltage pulse on  $\text{Bi}_2\text{Se}_3$ . Meanwhile, our soft-PCS with silver paint shows a  
 95 consistent behaviour: the ZBCP would disappear in the conductance curves while the zero-bias  
 96 conductance as a function of temperature shows the absence of any SC transition after thermal  
 97 cycles as in Fig. 2d. It is thus a strong evidence for the metastable nature of induced SC in the

108 mesoscopic Ag point-contacts on  $\text{Bi}_2\text{Se}_3$ , which can be repetitively erased by thermal activations.

109 As for the underlying mechanism of the induced superconductivity in the Ag- $\text{Bi}_2\text{Se}_3$  type  
110 point-contacts, the voltage pulse can usually generate a considerable local electric field and  
111 inject the metallic atoms from the tip to  $\text{Bi}_2\text{Se}_3$  [32]. The injected Ag atoms should probably be  
112 trapped by and intercalated into the vdW gap of  $\text{Bi}_2\text{Se}_3$  at low temperatures, forming some kind  
113 of  $\text{Ag}_x\text{Bi}_2\text{Se}_3$  with superconductivity in the local region similar to the SC compound  $\text{Cu}_x\text{Bi}_2\text{Se}_3$ .  
114 We notice that SC in  $\text{Ag}_x\text{Bi}_2\text{Se}_3$  has been theoretically proposed via the dynamic mean-field  
115 theory with a local density approximation and its  $T_c$  is estimated around 4.5 K, pretty similar  
116 to our experimental results [33]. It is actually a common practice for atoms to be deposited on  
117 substrates in scanning probe microscopic lithography with the help of a voltage pulse on metallic  
118 tip [34, 35, 36]. In general, the atomic emission process is strongly dependent on the evaporation  
119 field for different atoms, where Ag has a relatively lower evaporation field in comparison with  
120 Cu and Au [32, 37, 38]. On the other hand, even though Ti has a much lower evaporation field  
121 than Ag, the intercalation of Ti in  $\text{Bi}_2\text{Se}_3$  probably would not induce SC as in  $\text{Ag}_x\text{Bi}_2\text{Se}_3$  [33].  
122 Of course, the real atomic emission process can be more complicated and more detailed studies  
123 are further needed [32, 39].

124 The disappearance of superconductivity in the Ag- $\text{Bi}_2\text{Se}_3$  mesoscopic point-contacts over  
125 thermal cycles probably originates from the instability of Ag intercalation in the  $\text{Bi}_2\text{Se}_3$  vdW  
126 gaps at high temperatures. Considering the weak vdW gap between the  $\text{Bi}_2\text{Se}_3$  quintuple layers,  
127 it is not surprising that no  $\text{Ag}_x\text{Bi}_2\text{Se}_3$  compound has been reported to be synthesized at room  
128 temperatures so far. At 300 K, the intercalated Ag atoms would have escaped from the vdW  
129 gap thanks to the thermal activation energy. In comparison, even though SC in  $\text{Cu}_x\text{Bi}_2\text{Se}_3$   
130 crystals has been widely reported, its superconducting volume fraction shows a high dependence  
131 on quench conditions, where quenching from a lower temperature or not quenching at all can  
132 be detrimental to SC, strongly supporting the metastable nature of Cu intercalation [40]. A  
133 metastable superconductivity by thermal cycles has also been reported in  $\text{IrTe}_2$  with charge-  
density-wave (CDW) order as its ground state. For  $\text{IrTe}_2$ , a thermal quench process achieved  
by current pulses can induce or erase the SC in a tiny exfoliated sample, and it is a kinetic and  
nonequilibrium approach to induce SC as a metastable state competing with the CDW order  
[41, 42]. In our case of  $\text{Bi}_2\text{Se}_3$ , the voltage pulse on point-contact can locally heat it to high  
temperatures and then rapidly cool down, mimicking the thermal quench process. However, the  
absence of SC in Au, Cu and Ti point-contacts on  $\text{Bi}_2\text{Se}_3$  argues against the same SC mechanism  
as in  $\text{IrTe}_2$ , but favors the importance of Ag intercalation.

134 The erasable SC in mesoscopic point-contacts on  $\text{Bi}_2\text{Se}_3$  with thermal cycles implies a promis-  
135 ing application on logic and memory circuits as an electrical switch, if equipped with a local  
136 heater on the contact [43, 44, 45, 46]. A voltage pulse can momentarily drive the sample into

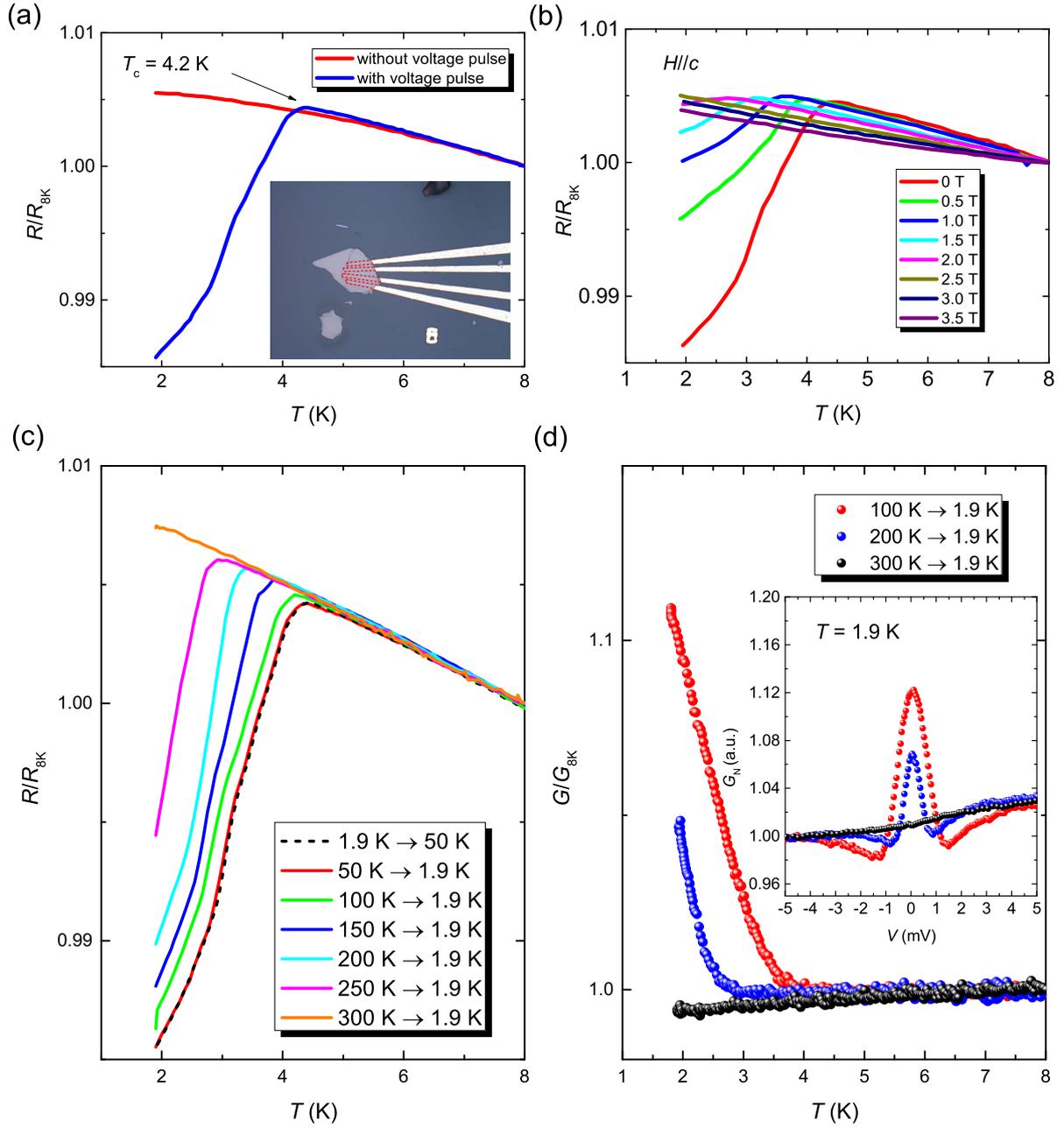


Figure 2: **Evidence of local and erasable superconductivity in Ag-Bi<sub>2</sub>Se<sub>3</sub> contacts.**

(a) Temperature dependence of the electrical resistance for an exfoliated Bi<sub>2</sub>Se<sub>3</sub> flake before and after voltage pulse for comparison. The inset is the photo of an exfoliated flake with Ag electrodes pre-deposited on the bottom with the electrode distance  $\sim 3 \mu\text{m}$ . (b) The evolution of R-T curves in different magnetic fields for the exfoliated Bi<sub>2</sub>Se<sub>3</sub> sample after voltage pulse. (c) & (d) Temperature dependence of the electrical resistance for exfoliated Bi<sub>2</sub>Se<sub>3</sub>, and ZBC for silver paint point-contacts after different thermal cycles with a temperature ramping speed of 3 K/min. The inset of (d) shows the Ag-Bi<sub>2</sub>Se<sub>3</sub> point-contact conductance at 1.9 K after different thermal cycles.

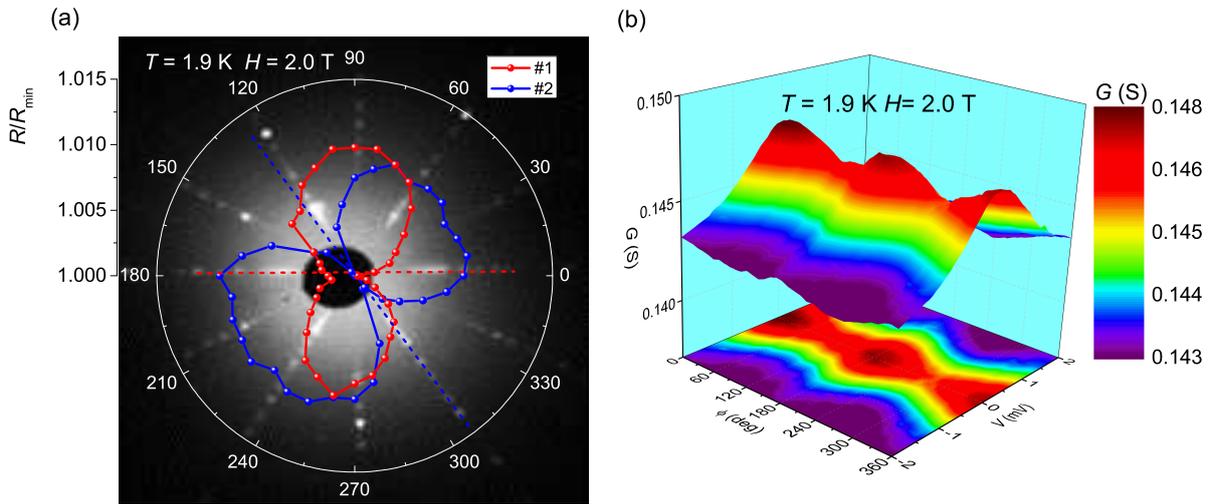


Figure 3: **Field-angle dependence of the soft-PCS of Ag-Bi<sub>2</sub>Se<sub>3</sub> with the induced superconductivity.** (a) Field-angle dependence of the ZBR for two contacts #1 and #2 on the same Bi<sub>2</sub>Se<sub>3</sub> crystal at 1.9 K with an in-plane field of 2.0 T. The red (blue) dashed line marks the short  $C_2$  axis for its nematic domain #1 (#2), respectively. (b) Three-dimensional contour plot of the soft-PCS conductance curves as a function of field angle at 1.9 K and 2.0 T.

134 superconducting state as a low-resistance phase, while an electrical heater can switch it back to  
 135 the normal state as a high-resistance phase. This can serve as a phase-change memory while its  
 136 different resistance states represent 1s and 0s for the stored digital data. The local and erasable  
 137 superconductivity induced with Ag tip signifies a more accurate and controllable writing/design  
 138 of superconducting circuits (even topological superconducting circuits) at low temperatures, if  
 139 scanning probe microscopic lithography method can be introduced [36, 47]. We notice a re-  
 140 cent work carried out by the conductive-AFM method on two-dimensional electron gas and our  
 141 results would facilitate such efforts [48, 49].

142 Finally, we would like to investigate the superconducting nature of the Ag-doped topological  
 143 insulator Bi<sub>2</sub>Se<sub>3</sub> in our mesoscopic point-contacts, where our field-rotational PCS characterizes  
 144 a rotational  $C_4$  symmetry breaking and suggests an exotic topological SC as in Cu<sub>x</sub>Bi<sub>2</sub>Se<sub>3</sub>  
 145 [12, 13, 14, 15, 11, 17, 18]. The azimuthal field-angle dependence of the zero-bias point-contact  
 146 resistance (ZBR) on Bi<sub>2</sub>Se<sub>3</sub> after voltage pulse at 1.9 K and in field of 2.0 T is shown in Fig.  
 147 3a, where the magnetic field is rotated in the  $ab$ -plane. A clear 2-fold symmetry of the ZBR  
 148 is present at 2.0 T, probably signaling a  $C_2$  symmetry of the superconductor gap and thus a  
 149 nematic SC despite of its hexagonal lattice structure. This 2-fold symmetry is only observed in  
 150 the superconducting state below its upper critical field  $H_{c2} \sim 3.0$  T but absent in the normal  
 151 state as shown in Fig. S2(a). When fixing the field at 2.0 T, the nematic behaviour disappears  
 152 exactly around its local  $T_c$  as in Fig. S2(b) and Fig. S2(c). In our PCS configuration, the  
 153 junction current is always along the  $c$ -axis and perpendicular to the rotational field, so that the

154 influence of vortex motion and Lorentz effect can be excluded. In Fig. 3a, the azimuthal field-  
 155 angle dependence of ZBR for two different point-contacts #1 and #2 on the same sample both  
 156 shows an obvious dumbbell shape but with different long  $C_2$  axis, which are perpendicular to the  
 157 crystal axis and imply the existence of nematic SC domains in  $\text{Bi}_2\text{Se}_3$  below  $T_c$ . It is a strong  
 158 evidence to exclude other artificial effects as the two-fold origins, such as sample misalignment,  
 159 sample geometry or point-contact geometry. The existence of different nematic domains is  
 160 probably caused by the local strain effect and its microscopic mechanism needs further careful  
 161 studies.

162 Field-angle dependence of PCS conductance curves at 1.9 K and 2.0 T is shown in Fig. 3b as  
 163 a three-dimensional contour plot, where a clear 2-fold symmetry can also be observed from both  
 164 the peak intensity and width of Andreev reflection signals. The anisotropic magnitude of the  
 165 nematic behaviour can be roughly estimated by the ratio of maximum/minimum conductance  
 166 peak width with  $1.5/1 \sim 1.5$ , which is the result of anisotropic upper critical field  $H_{c2}$  in the  
 167  $ab$ -plane. In the Ginzburg-Landau theory, the  $H_{c2}$  is inversely proportional to the square-root  
 168 product of coherence length  $\xi$  in two separate directions orthogonal to the field. We can infer  
 169 that the maximum of coherence length as well as the SC gap minimum in the  $ab$ -plane should  
 170 be along the crystal axis. Such superconductivity is consistent with a fully gapped  $\Delta_{4y}$  state  
 171 in an odd-parity  $E_u$  symmetry, implying a topological superconductor in the  $D_{3d}$  crystal point  
 172 group [12, 18]. A similar ZBCP in the PCS on  $\text{Cu}_x\text{Bi}_2\text{Se}_3$  has been claimed due to Majorana  
 173 fermions [12, 30], however, we note it can also arise from thermal effect for point-contacts in  
 174 thermal regimes [31, 50]. Further studies are required to explore the nature and origin of ZBCP  
 175 for the induced SC in our Ag- $\text{Bi}_2\text{Se}_3$  point-contacts.

176 In conclusion, we have discovered the unexpected superconductivity only in the Ag- $\text{Bi}_2\text{Se}_3$   
 177 mesoscopic point-contacts by applying a voltage pulse, either in soft- or mechanical- PCS setup,  
 178 which is rather absent in the case of Au, Cu or Ti contacts within the voltage limit. We  
 179 propose that the voltage pulse and thus electrical field should inject Ag atoms into the vdW  
 180 gap of  $\text{Bi}_2\text{Se}_3$  and induce a local superconductivity. The superconductivity can be erased by  
 181 thermal cycles, where warming samples up to high temperatures seems to lose the trapped Ag  
 182 atoms from the weak vdW gap. Our discovery of the erasable and repetitive superconductivity  
 183 in topological insulator  $\text{Bi}_2\text{Se}_3$  may pave a new route for applications of quantum electronic  
 184 devices that harness the power of topological superconductivity and Majorana fermions.

## 185 **Methods**

186 **Resistivity measurement.** Electrical resistivity of  $\text{Bi}_2\text{Se}_3$  was measured by the conven-  
 187 tional four-probe method. Electrodes on bulk sample of a larger size were made with silver  
 188 paint (SPI05001-AB), which can be dry within several minutes, while those on the exfoliated  
 189  $\text{Bi}_2\text{Se}_3$  flake were made with pre-sputtered Ag electrodes on Si/ $\text{SiO}_2$  chip and the  $\text{Bi}_2\text{Se}_3$  flake

190 was mechanically transferred on the top of Ag electrodes.

191 **Point-contact spectroscopy measurements.** Soft point-contacts on  $\text{Bi}_2\text{Se}_3$  were pre-  
192 pared by attaching a 20  $\mu\text{m}$  diam. gold wire with a silver-paint drop at the end on the freshly-  
193 cleaved surface at room temperature. In such a configuration, thousands of parallel nanoscale  
194 channels were assumed between individual silver particles and the crystal surface. Mechanical  
195 point-contacts on  $\text{Bi}_2\text{Se}_3$  in a needle-anvil style were prepared by engaging a sharp tip on the  
196 sample surface by piezo-controlled nano-positioners. The tips can be Ag, Au, Cu and Ti wires,  
197 with sharp apex cut by razor blade. The conductance curves as a function of bias voltage,  
198  $G(V)$ , were recorded with the conventional lock-in technique in a quasi-four-probe configura-  
199 tion. The output current is mixed with dc and ac components, which were supplied by the  
200 model 6221 Keithley current source and model 7265 DSP lock-in amplifier, respectively. The  
201 first harmonic response of the lock-in amplifier is proportional to its point-contact resistance  
202  $dV/dI$  as a function of the biased-voltage  $V$ .

203 **Low temperature measurements.** Resistivity and point-contact spectroscopy down to  
204 1.9 K were measured in a Quantum Design Physical Property Measurement System (14T-PPMS)  
205 equipped with a sample rotator.

#### 206 **Data availability**

207 The authors declare that all relevant data supporting the findings of this study are available  
208 within the paper and its Supplementary Information files.

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218 **Author contributions** The project was conceived by Tian Le, Xiaozhi Wang and Xin Lu;  
219  $\text{Bi}_2\text{Se}_3$  device on Ag electrodes was designed by Qikai Ye and Xiaozhi Wang. Laue diffraction,  
220 resistivity and point-contact spectroscopy measurements were performed by Tian Le and ana-  
221 lyzed by Tian Le, Chufan Chen, Lichang Yin, Dongting Zhang, and Xin Lu; Tian Le and Xin  
222 Lu wrote the manuscript with input from all authors.

223 **Competing financial interests** The authors declare that they have no conflict of interest.

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# Figures

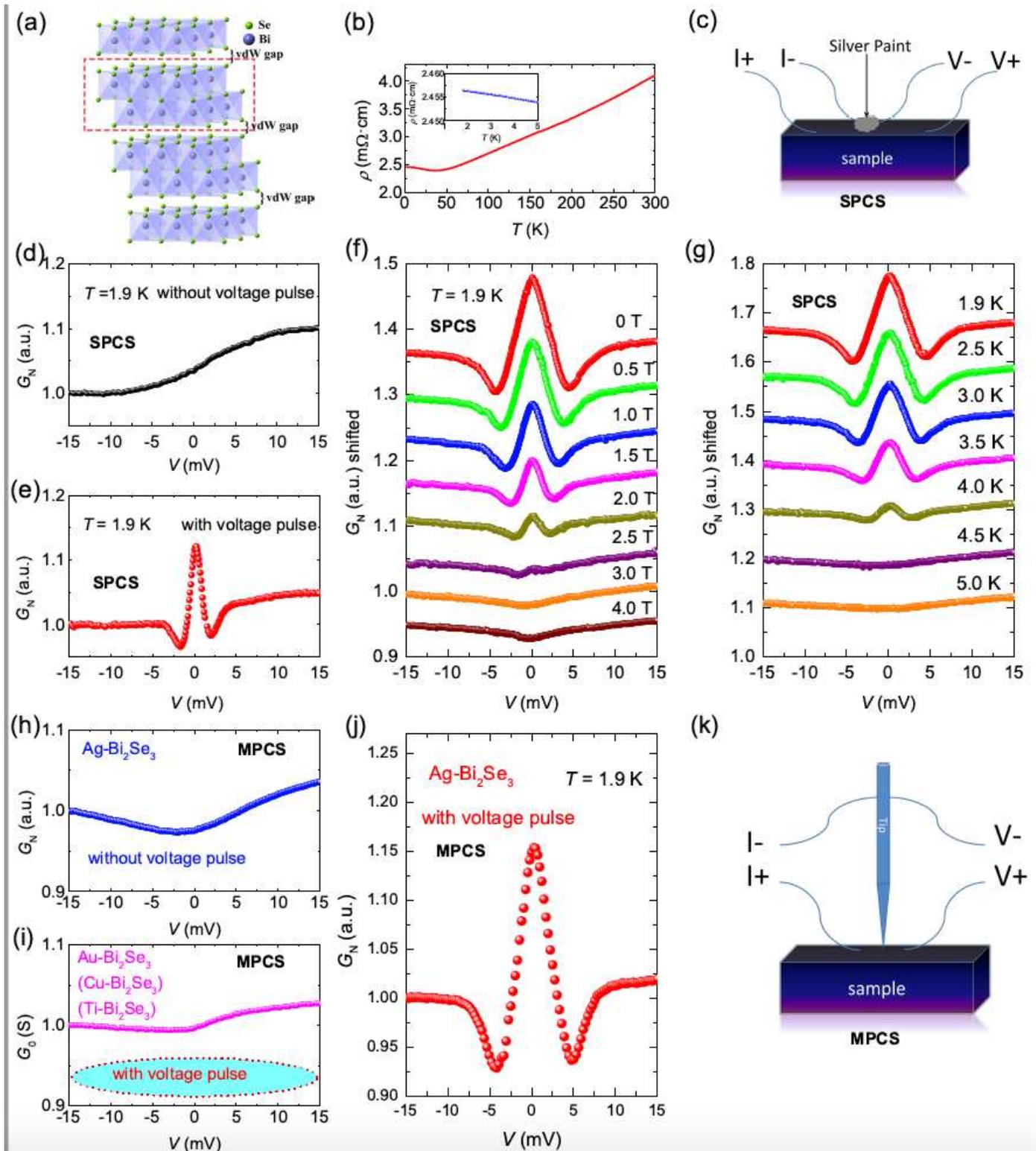
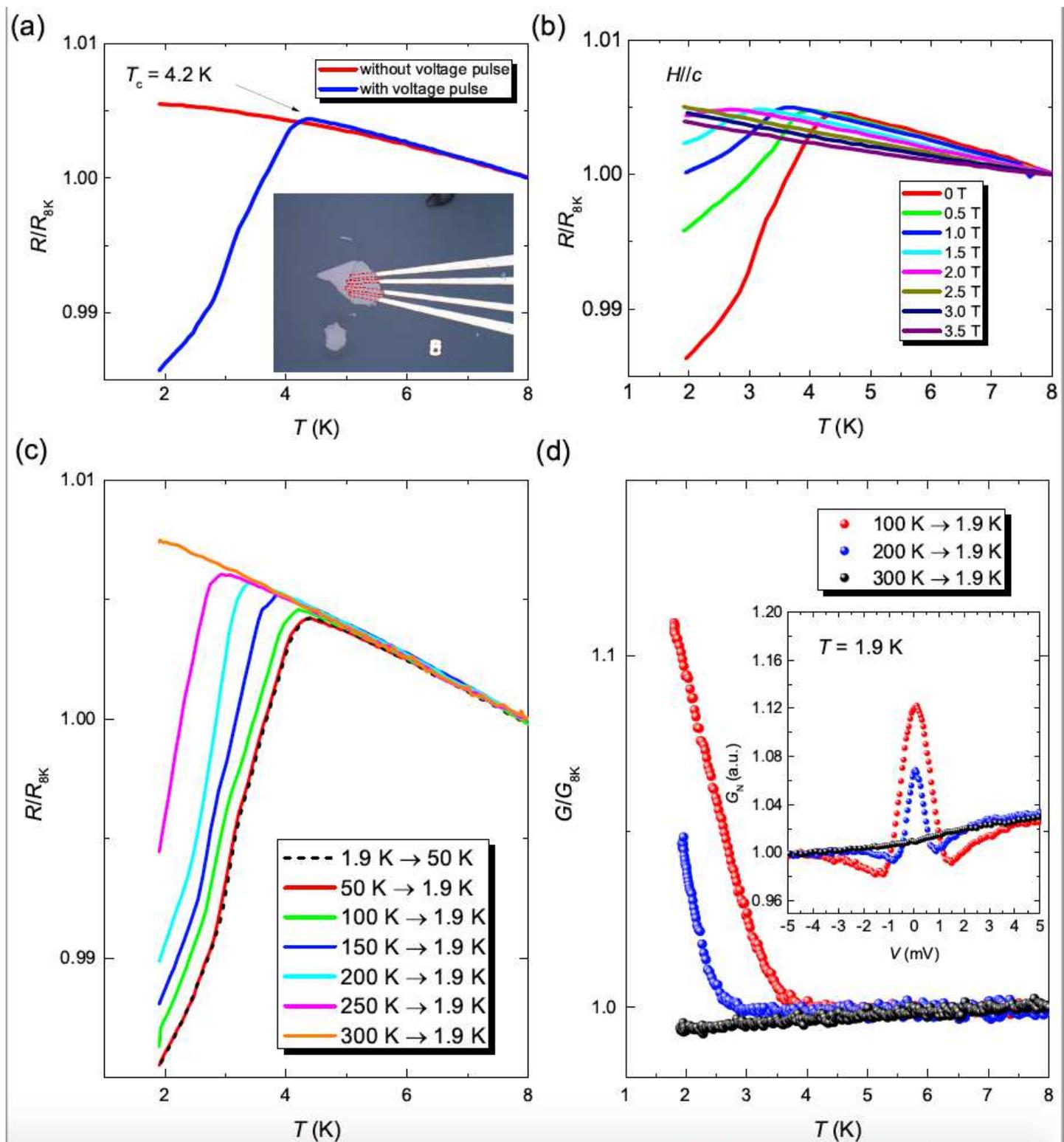


Figure 1

Evidence for induced superconductivity in mesoscopic Ag point-contact on Bi<sub>2</sub>Se<sub>3</sub>. (a) The crystal structure of topological insulator Bi<sub>2</sub>Se<sub>3</sub> with vdW gap between adjacent Se-Bi-Se-Bi-Se quintuple layers. (b) Temperature dependence of the electrical resistivity for the pristine Bi<sub>2</sub>Se<sub>3</sub> sample with a dimension

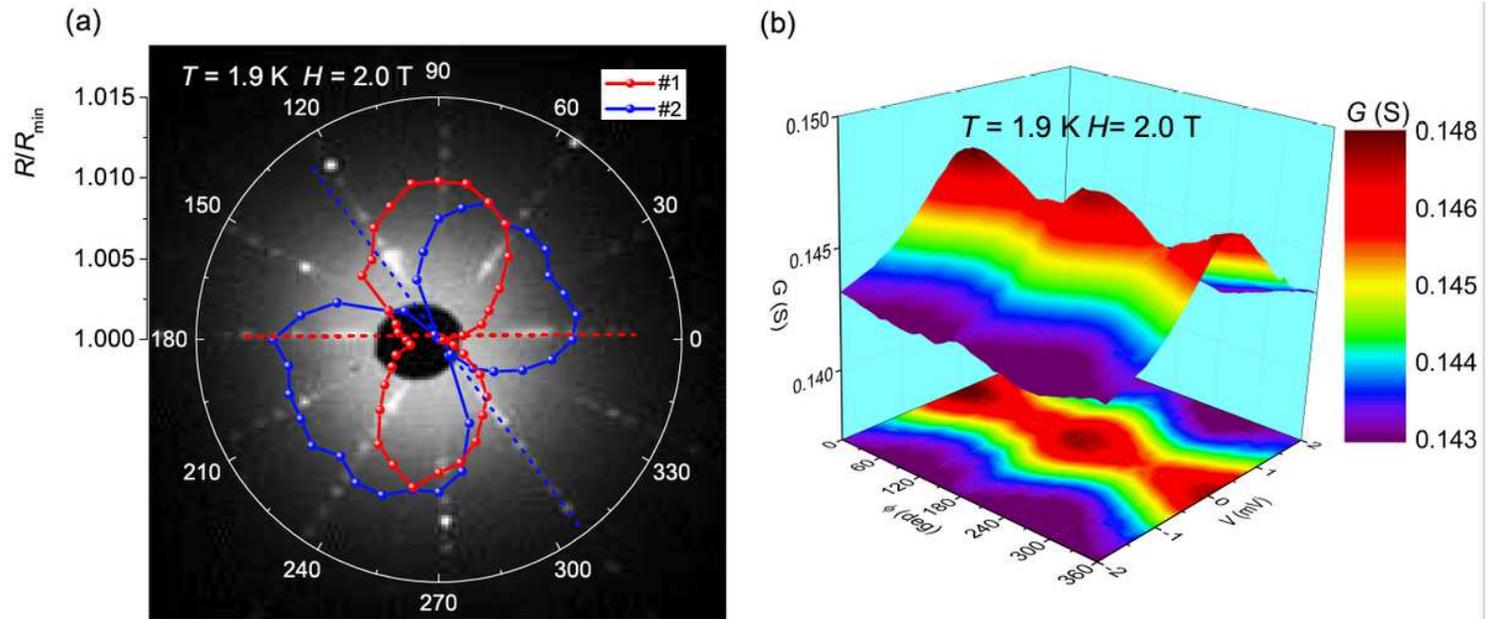
of  $1073 \mu\text{m} \times 591 \mu\text{m} \times 6.3 \mu\text{m}$ . (c) Schematic illustration of the soft-PCS electrode configuration on  $\text{Bi}_2\text{Se}_3$ . (d) A representative soft-PCS conductance curve for silver paint on the  $\text{Bi}_2\text{Se}_3$  crystal at 1.9 K without any voltage pulse. GN is the normalized conductance divided by the conductance value at high voltages. (e) A reproducible ZBCP feature in the soft-PCS at 1.9 K after voltage pulse on the contact. (f) & (g) Magnetic field and temperature evolution of the soft-PCS conductance curves with induced superconductivity in the contact region, respectively. (h) & (i) Mechanical-PCS conductance curve at 1.9 K for Ag tip before voltage pulse and for Au, Cu or Ti tip after voltage pulse, respectively. (j) Mechanical-PCS conductance curve at 1.9 K for Ag tip with induced SC after voltage pulse. (k) Schematic illustration of the needle-anvil configuration of mechanical point-contacts.



**Figure 2**

Evidence of local and erasable superconductivity in Ag-Bi<sub>2</sub>Se<sub>3</sub> contacts. (a) Temperature dependence of the electrical resistance for an exfoliated Bi<sub>2</sub>Se<sub>3</sub> flake before and after voltage pulse for comparison. The inset is the photo of an exfoliated flake with Ag electrodes pre-deposited on the bottom with the electrode distance  $\sim 3$   $\mu$ m. (b) The evolution of R-T curves in different magnetic fields for the exfoliated Bi<sub>2</sub>Se<sub>3</sub> sample after voltage pulse. (c) & (d) Temperature dependence of the electrical resistance for exfoliated

Bi<sub>2</sub>Se<sub>3</sub>, and ZBC for silver paint point-contacts after different thermal cycles with a temperature ramping speed of 3 K/min. The inset of (d) shows the Ag-Bi<sub>2</sub>Se<sub>3</sub> point-contact conductance at 1.9 K after different thermal cycles.



**Figure 3**

Field-angle dependence of the soft-PCS of Ag-Bi<sub>2</sub>Se<sub>3</sub> with the induced superconductivity. (a) Field-angle dependence of the ZBR for two contacts #1 and #2 on the same Bi<sub>2</sub>Se<sub>3</sub> crystal at 1.9 K with an in-plane field of 2.0 T. The red (blue) dashed line marks the short C2 axis for its nematic domain #1 (#2), respectively. (b) Three-dimensional contour plot of the soft-PCS conductance curves as a function of field angle at 1.9 K and 2.0 T.

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